

RF Power Field Effect Transistor**N-Channel Enhancement-Mode Lateral MOSFET**

Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for FM, TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

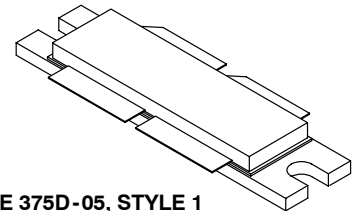
- W-CDMA Performance @ -45 dBc, 5 MHz Offset, 15 DTCH, 1 Perch
Output Power — 14 Watts (Avg.)
Power Gain — 11.5 dB
Efficiency — 16%
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2140 MHz, 120 Watts CW Output Power

Features

- Internally Matched for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- RoHS Compliant
- In Tape and Reel. R6 Suffix = 150 Units per 56 mm, 13 inch Reel.

MRF21120R6

**2110-2170 MHz, 120 W, 28 V
LATERAL N-CHANNEL
RF POWER MOSFET**



**CASE 375D-05, STYLE 1
NI-1230**

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	389 2.22	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Case Operating Temperature	T_C	150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.45	$^\circ\text{C}/\text{W}$

Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M3 (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics ⁽¹⁾					
Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 20\text{ }\mu\text{Adc}$)	$V_{(BR)DSS}$	65	—	—	Vdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
On Characteristics					
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 2\text{ Adc}$)	g_{fs}	—	4.8	—	S
Gate Threshold Voltage ⁽¹⁾ ($V_{DS} = 10\text{ V}$, $I_D = 200\text{ }\mu\text{A}$)	$V_{GS(th)}$	2.5	3	3.8	Vdc
Gate Quiescent Voltage ⁽³⁾ ($V_{DS} = 28\text{ V}$, $I_D = 1000\text{ mA}$)	$V_{GS(Q)}$	3	3.9	5	Vdc
Drain-Source On-Voltage ⁽¹⁾ ($V_{GS} = 10\text{ V}$, $I_D = 2\text{ A}$)	$V_{DS(on)}$	—	0.38	0.5	Vdc
Dynamic Characteristics ^(1, 2)					
Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{rss}	—	2.8	—	pF
Functional Tests ⁽³⁾ (In Freescale Test Fixture, 50 ohm system)					
Common-Source Amplifier Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2170.0\text{ MHz}$, $f_2 = 2170.1\text{ MHz}$)	G_{ps}	10.5	11.4	—	dB
Drain Efficiency ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2170.0\text{ MHz}$, $f_2 = 2170.1\text{ MHz}$)	η	30	34.5	—	%
Intermodulation Distortion ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2170.0\text{ MHz}$, $f_2 = 2170.1\text{ MHz}$)	IMD	—	-31	-28	dB
Input Return Loss ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2170.0\text{ MHz}$, $f_2 = 2170.1\text{ MHz}$)	IRL	—	-12	-9	dB
Common-Source Amplifier Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2140.0\text{ MHz}$, $f_2 = 2140.1\text{ MHz}$)	G_{ps}	—	11.5	—	dB
Common-Source Amplifier Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2110.0\text{ MHz}$, $f_2 = 2110.1\text{ MHz}$)	G_{ps}	—	11.5	—	dB
Drain Efficiency ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2110.0\text{ MHz}$, $f_2 = 2110.1\text{ MHz}$)	η	—	34.5	—	%
Intermodulation Distortion ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2110.0\text{ MHz}$, $f_2 = 2110.1\text{ MHz}$)	IMD	—	-31	—	dB
Input Return Loss ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2110.0\text{ MHz}$, $f_2 = 2110.1\text{ MHz}$)	IRL	—	-12	—	dB

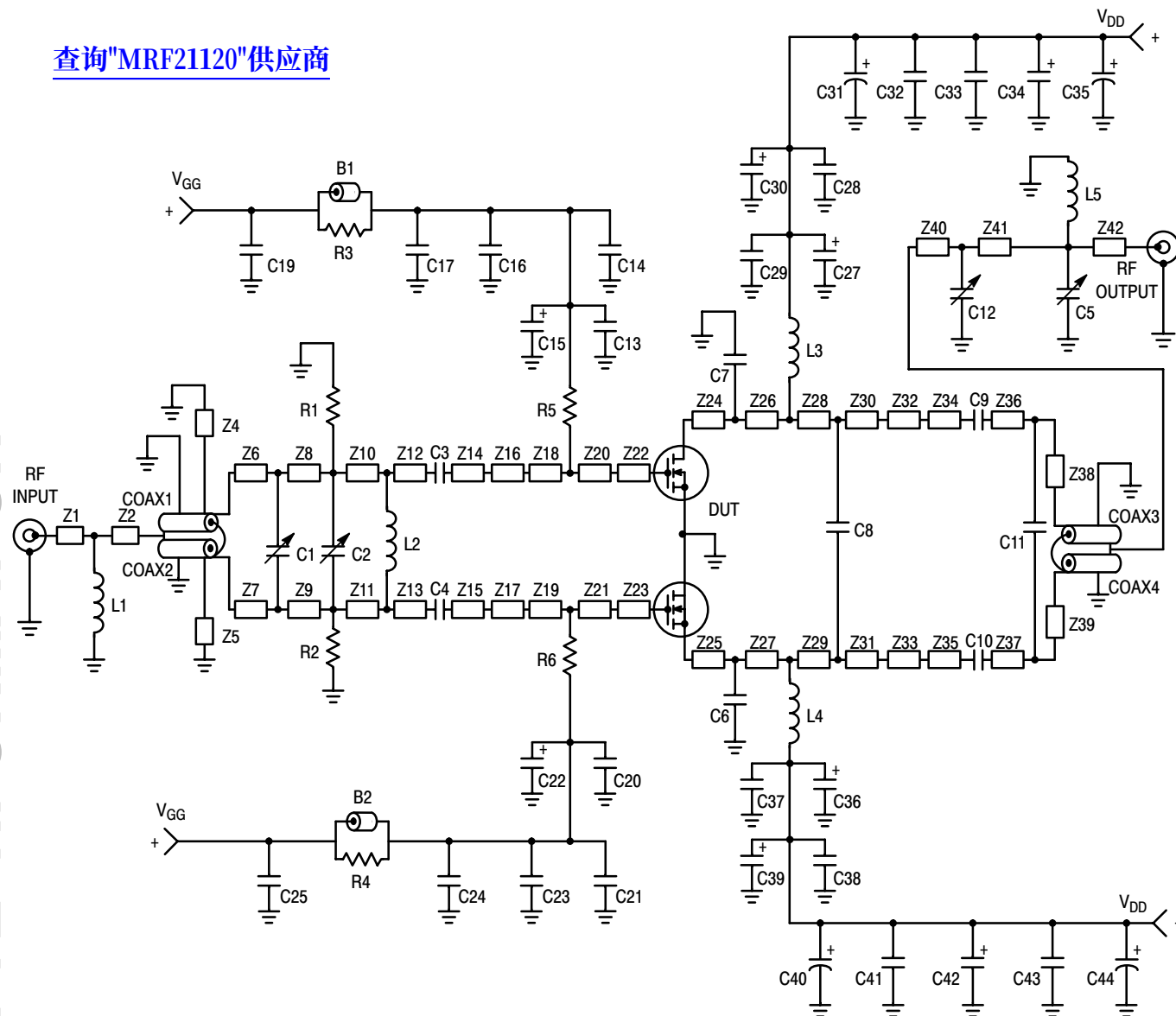
1. Each side of device measured separately.
2. Part internally matched both on input and output.
3. Device measured in push-pull configuration.

(continued)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted) **(continued)**

Characteristic	Symbol	Min	Typ	Max	Unit
Functional Tests (In Freescale Test Fixture, 50 ohm system) ⁽¹⁾ (continued)					
Power Output, 1 dB Compression Point ($V_{DD} = 28\text{ Vdc}$, CW, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2170.0\text{ MHz}$)	P1dB	—	120	—	W
Common-Source Amplifier Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W CW}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2170.0\text{ MHz}$)	G_{ps}	—	10.5	—	dB
Drain Efficiency ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 120\text{ W CW}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 2170.0\text{ MHz}$)	η	—	42	—	%

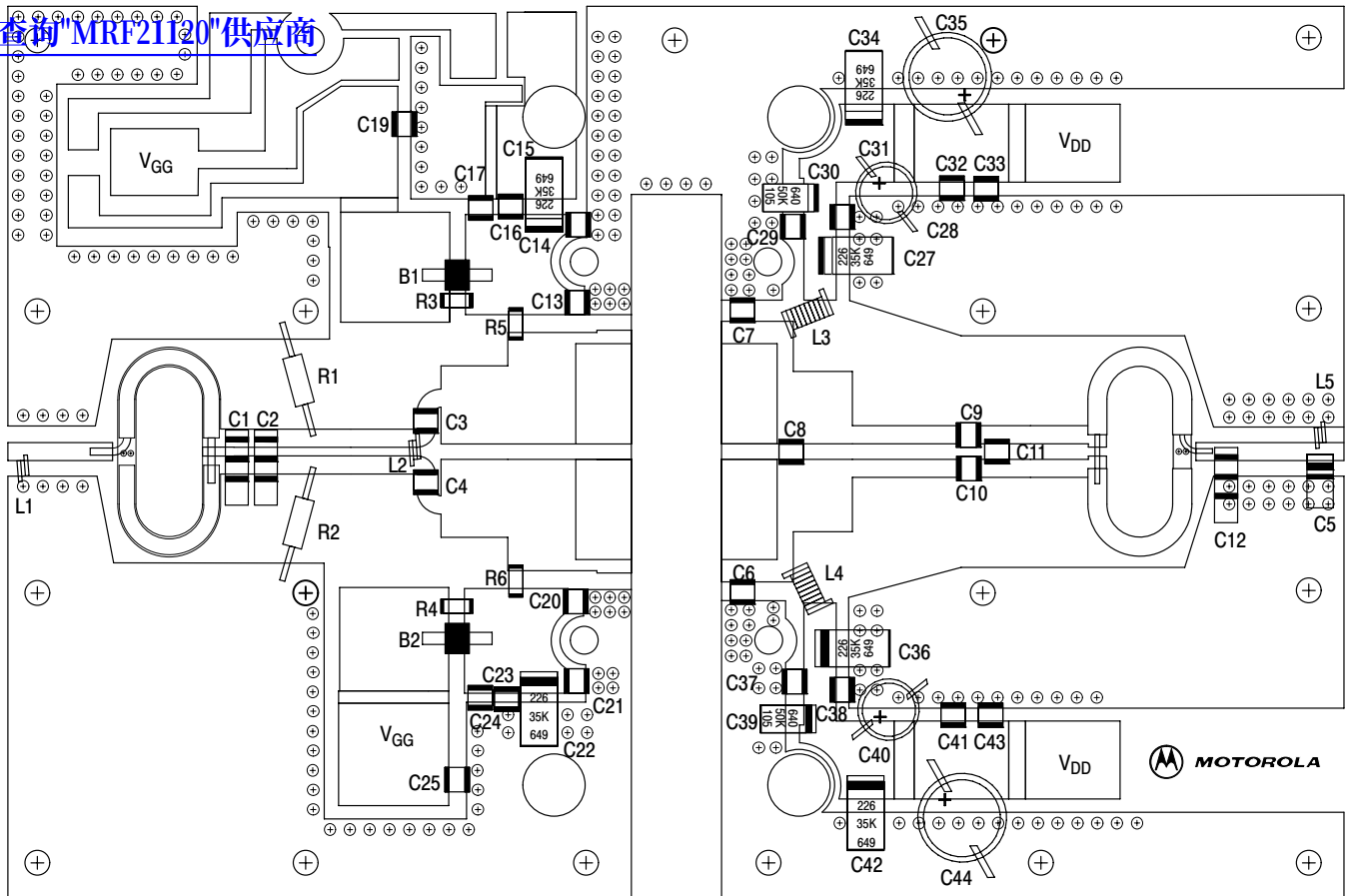
1. Device measured in push-pull configuration.



B1, B2	Ferrite Beads, Fair Rite
C1, C2, C12	0.6 - 4.5 pF Variable Capacitors, Johanson Gigatrim
C3, C4, C9, C10	10 pF Chip Capacitors, ATC
C5	0.4 - 2.5 pF Variable Capacitor, Johanson Gigatrim
C6, C7	2.0 pF Chip Capacitors, ATC
C8	0.5 pF Chip Capacitor, ATC
C11	0.2 pF Chip Capacitor, ATC
C13, C20, C29, C37	5.1 pF Chip Capacitors, ATC
C14, C21, C28, C38	91 pF Chip Capacitors, ATC
C15, C22, C27, C34, C36, C42	22 μ F, 35 V Tantalum Surface Mount Chip Capacitors, Kemet
C16, C23, C33, C43	0.039 μ F Chip Capacitors, ATC
C17, C24, C32, C41	1000 pF Chip Capacitors, ATC
C19, C25	0.022 μ F Chip Capacitors, ATC
C30, C39	1.0 μ F, 35 V Tantalum Surface Mount Chip Capacitors, Kemet
C31, C40	100 μ F, 50 V Electrolytic Capacitors, Sprague
C35, C44	470 μ F, 63 V Electrolytic Capacitors, Sprague
Coax1, Coax2	25 Ω Semi Rigid Coax, 70 mil OD, 1.05" Long
Coax3, Coax4	50 Ω Semi Rigid Coax, 85 mil OD, 1.05" Long
L1, L5	5.0 nH Minispring Inductors, Coilcraft
L2	8.0 nH Minispring Inductor, Coilcraft
L3, L4	7.15 nH Microspring Inductors, Coilcraft
R1, R2	1 k Ω , 1/4 W Fixed Metal Film Resistors, Dale
R3, R4	270 Ω , 1/8 W Fixed Film Chip Resistors, Dale
R5, R6	1.2 k Ω , 1/8 W Fixed Film Chip Resistors, Dale
Z1	0.150" x 0.080" Microstrip

Z2	0.320" x 0.080" Microstrip
Z4, Z5	1.050" x 0.080" Microstrip
Z6, Z7	0.120" x 0.080" Microstrip
Z8, Z9	0.140" x 0.080" Microstrip
Z10, Z11	0.610" x 0.080" Microstrip
Z12, Z13	0.135" x 0.080" Microstrip
Z14, Z15	0.130" x 0.080" Microstrip
Z16, Z17	0.300" x 0.350" Microstrip
Z18, Z19	0.150" x 0.500" Microstrip
Z20, Z21	0.075" x 0.500" Microstrip
Z22, Z23	0.330" x 0.500" Microstrip
Z24, Z25	0.100" x 0.550" Microstrip
Z26, Z27	0.175" x 0.550" Microstrip
Z28, Z29	0.045" x 0.550" Microstrip
Z30, Z31	0.190" x 0.325" Microstrip
Z32, Z33	0.080" x 0.325" Microstrip
Z34, Z35	0.515" x 0.080" Microstrip
Z36, Z37	0.020" x 0.080" Microstrip
Z38, Z39	0.565" x 0.080" Microstrip
Z40	0.100" x 0.080" Microstrip
Z41	0.470" x 0.080" Microstrip
Z42	0.100" x 0.080" Microstrip
Board Material	0.03" Teflon [®] , $\epsilon_r = 2.55$ Copper Clad, 2 oz. Cu
Connectors	N-Type Panel Mount, Stripline

Figure 1. 2110 - 2200 MHz Broadband Test Circuit Schematic



Freescall has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescall Semiconductor signature/logo. PCBs may have either Motorola or Freescall markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. 2110 - 2200 MHz Broadband Test Circuit Component Layout

TYPICAL CHARACTERISTICS

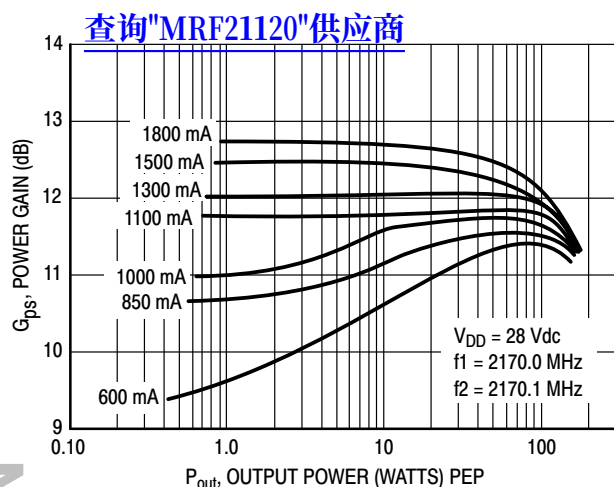


Figure 3. Power Gain versus Output Power

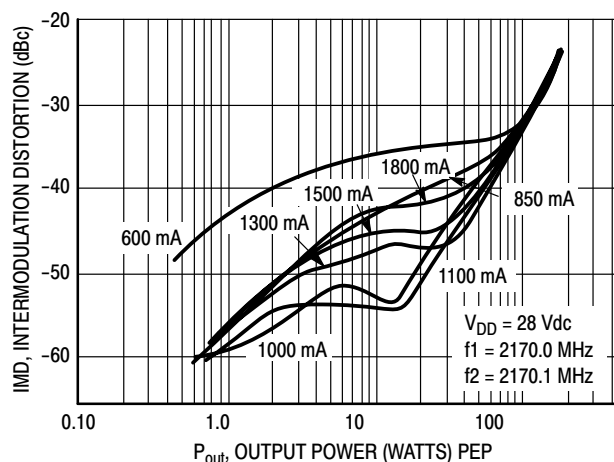


Figure 4. Intermodulation Distortion versus Output Power

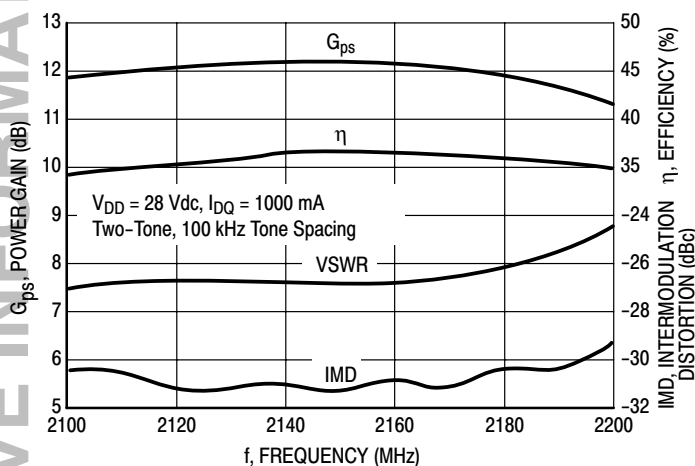


Figure 5. Class AB Broadband Circuit Performance

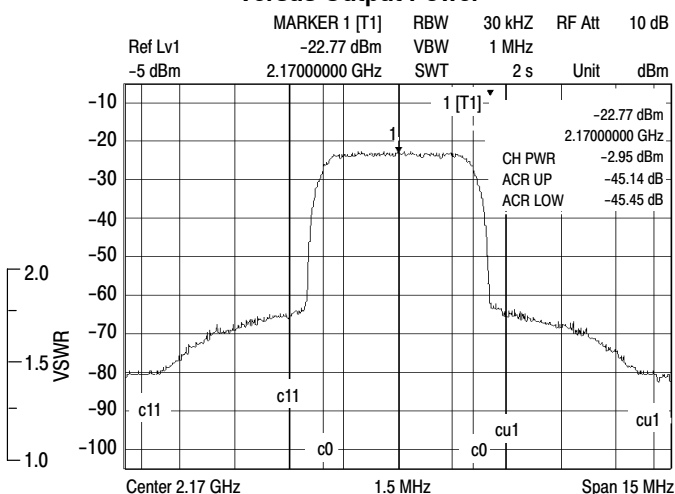


Figure 6. 2.17 GHz W-CDMA Mask at 14 Watts (Avg.), 5 MHz Offset, 15 DTCH, 1 Perch

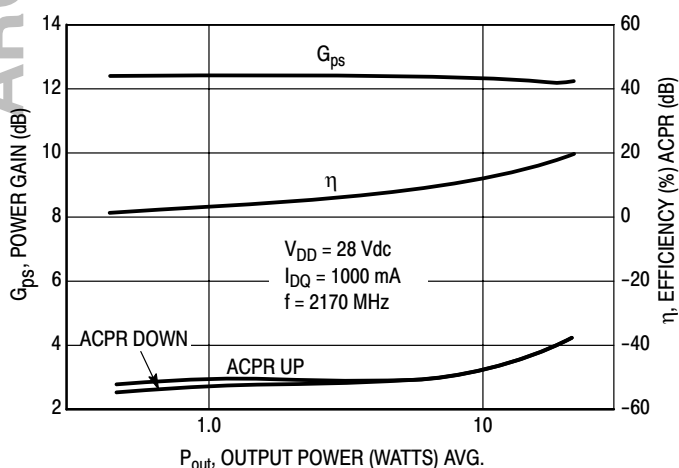


Figure 7. Power Gain, Efficiency, ACPR versus Output Power (W-CDMA)

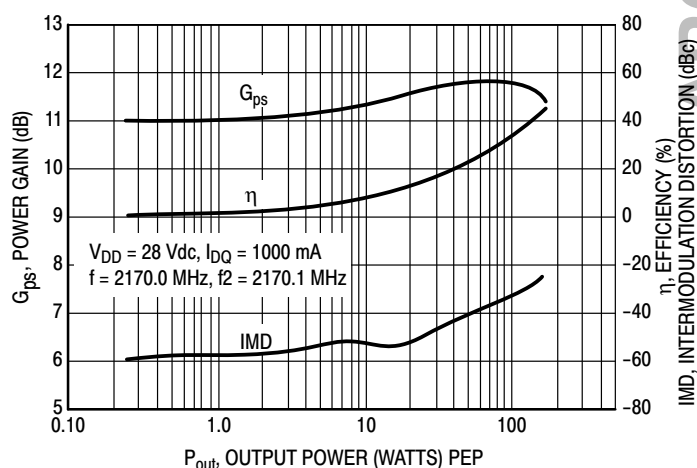
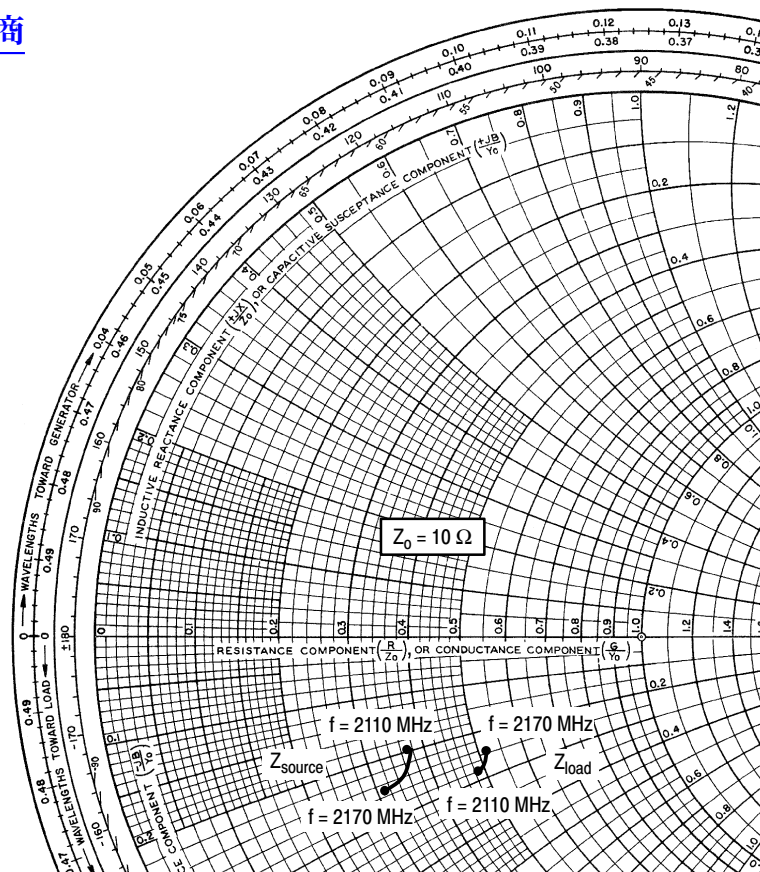


Figure 8. Power Gain, Efficiency, IMD versus Output Power



$V_{DD} = 28\text{ V}$, $I_{DQ} = 1000\text{ mA}$, $P_{out} = 120\text{ W PEP}$

f MHz	Z_{source} Ω	Z_{load} Ω
2110	$3.7 - j2.0$	$4.9 - j2.8$
2140	$3.5 - j2.4$	$5.1 - j2.7$
2170	$3.1 - j2.5$	$5.2 - j2.5$

Z_{source} = Test circuit impedance as measured from gate to gate, balanced configuration.

Z_{load} = Test circuit impedance as measured from drain to drain, balanced configuration.

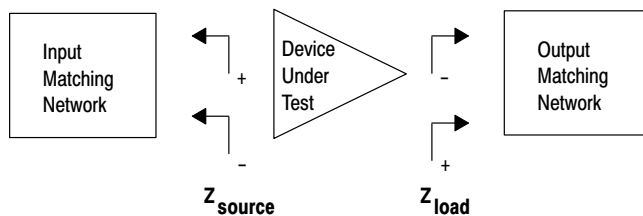


Figure 9. Series Equivalent Source and Load Impedance

NOTES

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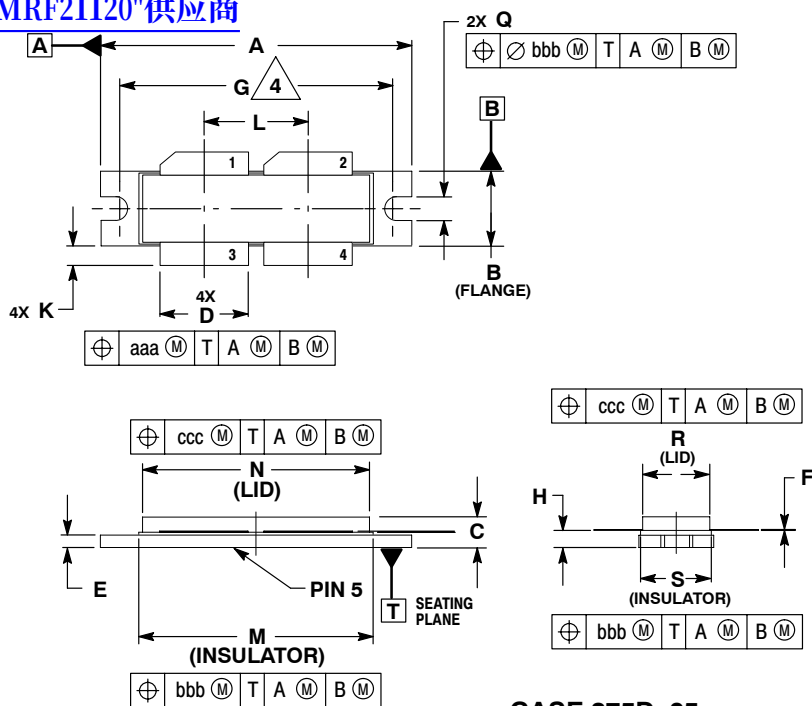
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PACKAGE DIMENSIONS



CASE 375D-05
ISSUE E
NI-1230

- NOTES:
1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
 4. RECOMMENDED BOLT CENTER DIMENSION OF 1.52 (38.61) BASED ON M3 SCREW.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.615	1.625	41.02	41.28
B	0.395	0.405	10.03	10.29
C	0.150	0.200	3.81	5.08
D	0.455	0.465	11.56	11.81
E	0.062	0.066	1.57	1.68
F	0.004	0.007	0.10	0.18
G	1.400	BSC	35.56	BSC
H	0.082	0.090	2.08	2.29
K	0.117	0.137	2.97	3.48
L	0.540	BSC	13.72	BSC
M	1.219	1.241	30.96	31.52
N	1.218	1.242	30.94	31.55
Q	0.120	0.130	3.05	3.30
R	0.355	0.365	9.01	9.27
S	0.365	0.375	9.27	9.53
aaa	0.013	REF	0.33	REF
bbb	0.010	REF	0.25	REF
ccc	0.020	REF	0.51	REF

STYLE 1:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. GATE
5. SOURCE

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USA/Europe or Locations Not Listed:
Freescale Semiconductor
Technical Information Center, CH370
1300 N. Alma School Road
Chandler, Arizona 85224
+1-800-521-6274 or +1-480-768-2130
support@freescale.com

Europe, Middle East, and Africa:
Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
support@freescale.com

Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor Hong Kong Ltd.
Technical Information Center
2 Dai King Street
Tai Po Industrial Estate
Tai Po, N.T., Hong Kong
+800 2666 8080
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